

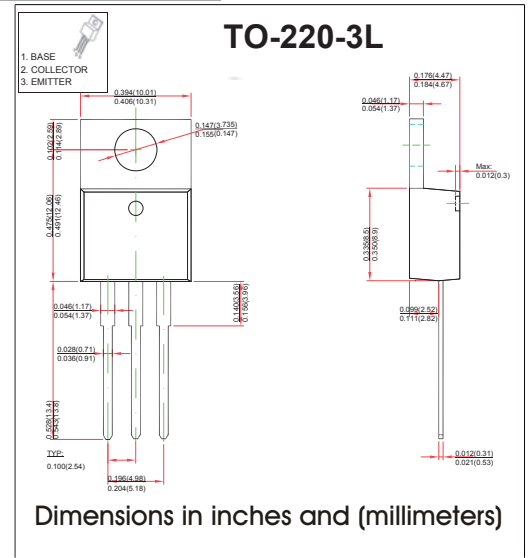
TO-220-3L Plastic-Encapsulate Transistors

FEATURES

- High DC Current Gain : $h_{FE}=1000$ @ $V_{CE}=4V$, $I_C=1A$ (Min.)
- Low Collector-Emitter Saturation Voltage Industrial Use
- DARLINGTON TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-220-3L molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	2	A
P_C	Collector Power Dissipation	2	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\text{mA}, I_E=0$	100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=30\text{mA}, I_B=0^{(SUS)}$	100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CEO}	$V_{CE}=50\text{V}, I_B=0$			2	mA
Collector cut-off current	I_{CBO}	$V_{CB}=100\text{V}, I_E=0$			1	mA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			2	mA
DC current gain	$h_{FE(1)}$	$V_{CE}=4\text{V}, I_C=1\text{A}$	1000			
	$h_{FE(2)}$	$V_{CE}=4\text{V}, I_C=2\text{A}$	500			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=8\text{mA}$			2.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=4\text{V}, I_C=2\text{A}$			2.8	V
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=0.1\text{MHz}$			100	pF